



THE DATASHEET OF STD70N6F3





STD70N6F3

N-channel 60 V, 8.0 mΩ, 70 A DPAK
STripFET™ III Power MOSFET

Preliminary data

Features

Type	V _{DSS}	R _{DS(on)}	I _D	P _w
STD70N6F3	60 V	< 10.5 mΩ	70 A	110 W

- Standard threshold drive
- 100% avalanche tested

Application

- Switching applications

Description

This STripFET™ III Power MOSFET technology is among the latest improvements, which have been especially tailored to minimize on-state resistance providing superior switching performance.

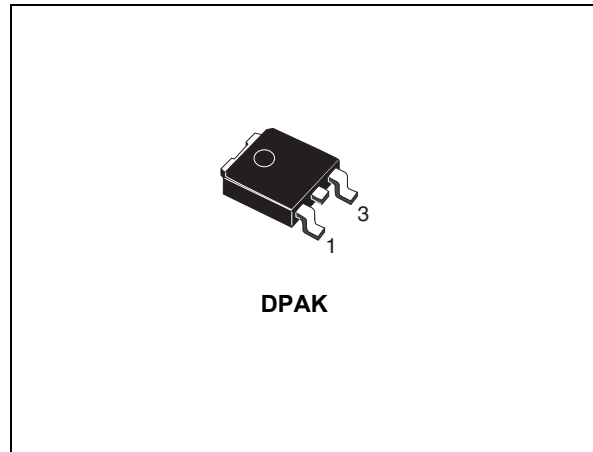


Figure 1. Internal schematic diagram

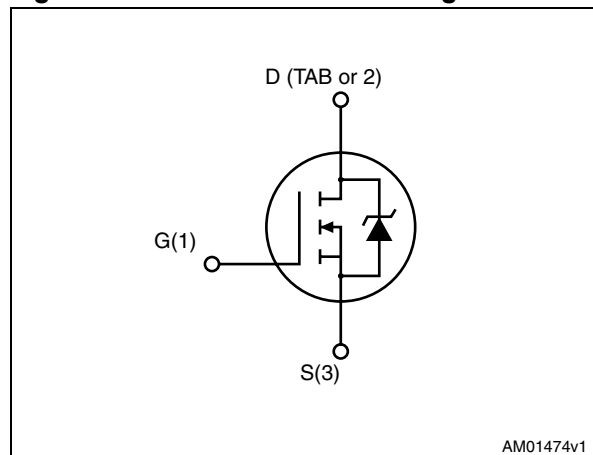


Table 1. Device summary

Order code	Marking	Package	Packaging
STD70N6F3	70N6F3	DPAK	Tape & reel

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS}=0$)	60	V
V_{GS}	Gate-Source voltage	± 20	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	70	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	50	A
$I_{DM}^{(1)}$	Drain current (pulsed)	280	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
	Derating factor	0.73	W/ $^\circ\text{C}$
$dv/dt^{(2)}$	Peak diode recovery voltage slope	TBD	V/ns
$E_{AS}^{(3)}$	Single pulse avalanche energy	TBD	mJ
T_j T_{stg}	Operating junction temperature Storage temperature	-55 to 175	$^\circ\text{C}$

1. Pulse width limited by safe operating area
2. $I_{SD} \leq 70\text{ A}$, $di/dt \leq 300\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{jmax}$
3. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_d = 35\text{ A}$, $V_{dd} = 40\text{ V}$

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.36	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	50	$^\circ\text{C}/\text{W}$

1. When mounted on FR-4 board of 1inch², 2oz Cu.

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 4. Static

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0$	60			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating},$ $V_{DS} = \text{Max rating}, T_c = 125^{\circ}C$			10 100	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20 V$			± 200	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2		4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 V, I_D = 35 A$		8.0	10.5	m Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 25 V, I_D = 35 A$	-	Tbd		S
C_{iss}	Input capacitance	$V_{DS} = 25 V, f = 1 MHz, V_{GS} = 0$	-	2200		pF
C_{oss}	Output capacitance			500		pF
C_{rss}	Reverse transfer capacitance			25		pF
Q_g	Total gate charge	$V_{DD} = 48 V, I_D = 70 A$	-	35	TBD	nC
Q_{gs}	Gate-source charge	$V_{GS} = 10 V$		15		nC
Q_{gd}	Gate-drain charge	(see Figure 5)		10		nC

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 6. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD}=30\text{ V}$, $I_D=35\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ <i>(see Figure 4),</i> <i>(see Figure 7)</i>	-	TBD TBD	-	ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD}=30\text{ V}$, $I_D=35\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ <i>(see Figure 4),</i> <i>(see Figure 7)</i>	-	TBD TBD	-	ns ns

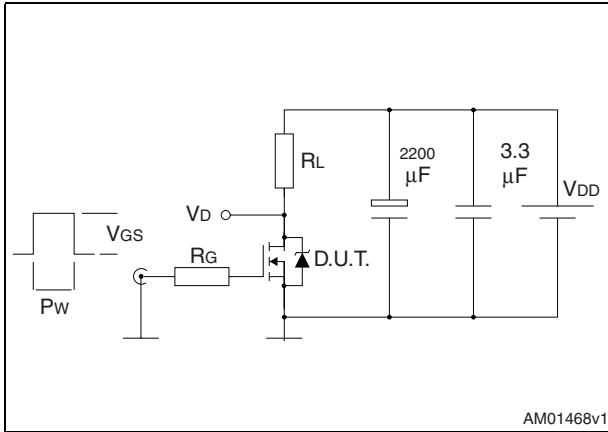
Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} I_{SDM}	Source-drain current Source-drain current (pulsed) ⁽¹⁾		-		70 280	A A
V_{SD}	Forward on voltage	$I_{SD}=70\text{ A}$, $V_{GS}=0$	-		1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=70\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD}=30\text{ V}$, $T_j=150\text{ }^\circ\text{C}$ <i>(see Figure 6)</i>	-	TBD TBD TBD		ns nC A

1. Pulsed: pulse duration = 300μs, duty cycle 1.5%

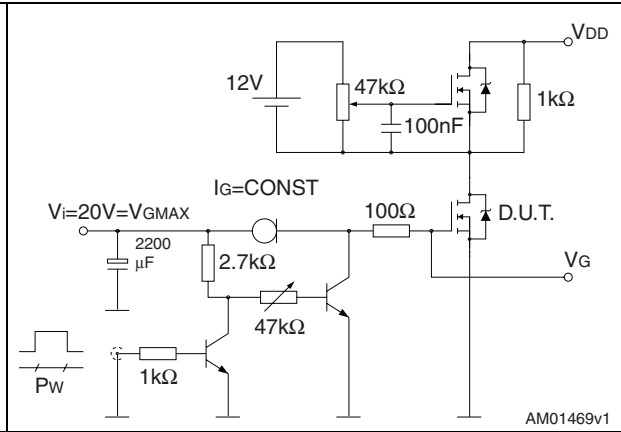
3 Test circuits

Figure 2. Switching times test circuit for resistive load



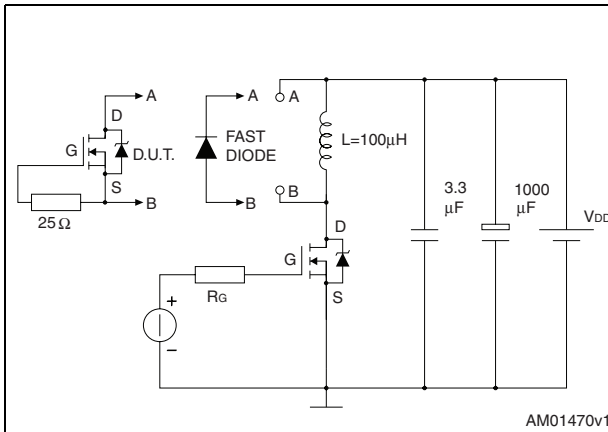
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Figure 3. Gate charge test circuit



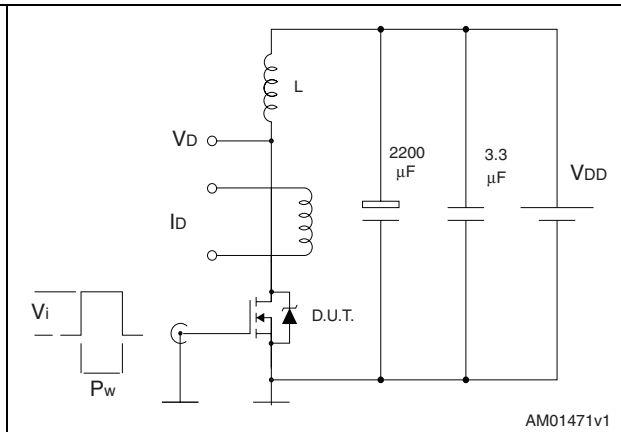
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Figure 4. Test circuit for inductive load switching and diode recovery times



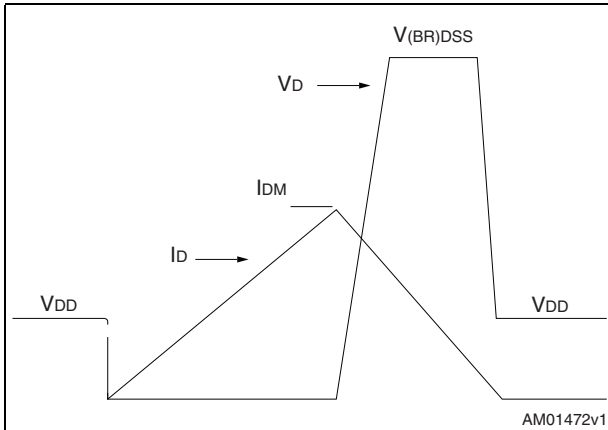
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Figure 5. Unclamped inductive load test circuit



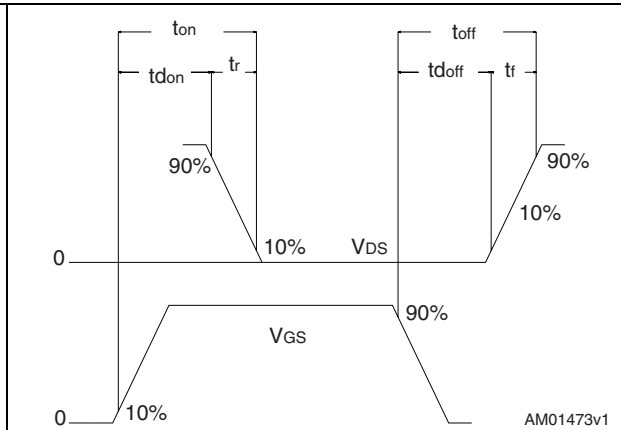
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Figure 6. Unclamped inductive waveform



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Figure 7. Switching time waveform



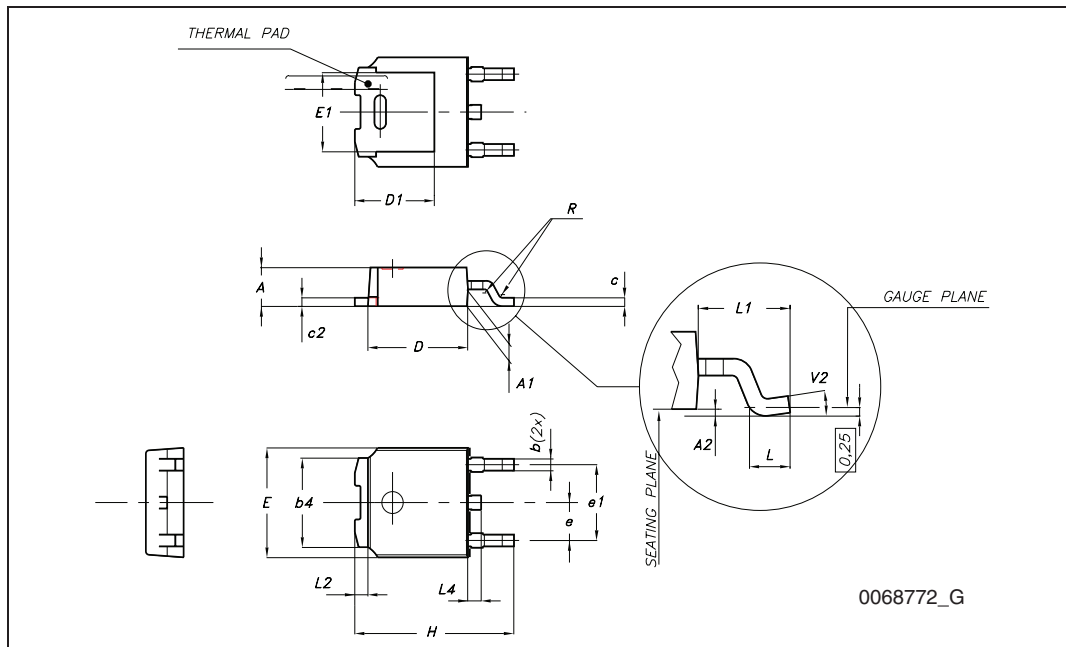
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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

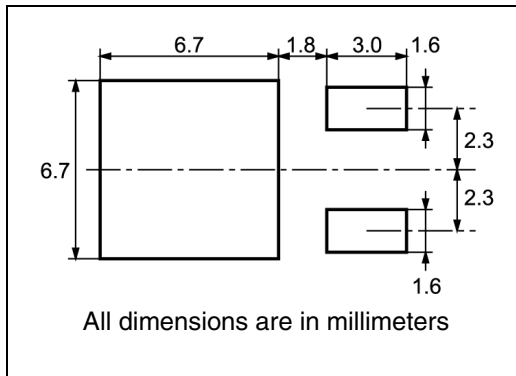
TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



5 Packaging mechanical data

DPAK FOOTPRINT



TAPE AND REEL SHIPMENT

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY		BULK QTY	
2500		2500	

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

6 Revision history

Table 8. Revision history

Date	Revision	Changes
11-Dec-2009	1	First release

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